

# isc N-Channel MOSFET Transistor

# IRFP4568, IIRFP4568

#### FEATURES

- Static drain-source on-resistance:  $Ros(on) \leq 5.9 m\Omega$
- Enhancement mode: Vth =3.0 to 5.0 V (VDS=VGS, ID=250  $\mu$  A)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### DESCRITION

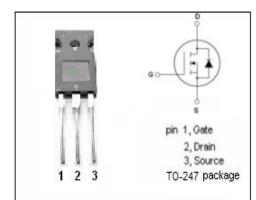
- · High Efficiency Synchronous Rectification in SMPS
- Uninterruptible Power Supply
- · High Speed Power Switching
- · Hard Switched And High Frequency Circuits

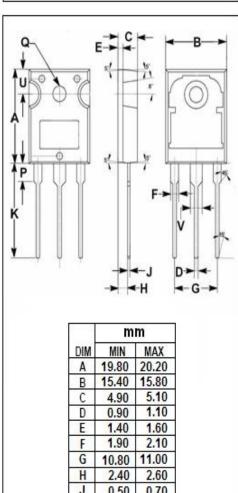
### • ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>DSS</sub>	Drain-Source Voltage	150	V	
V <sub>GS</sub>	Gate-Source Voltage	±30	V	
I <sub>D</sub>	Drain Current-Continuous	171	А	
I <sub>DM</sub>	Drain Current-Single Pulsed	684	А	
P <sub>D</sub>	Total Dissipation @T <sub>C</sub> =25℃	517	W	
Tj	Max. Operating Junction Temperature	175	$^{\circ}\mathbb{C}$	
T <sub>stg</sub>	Storage Temperature	-55~175	$^{\circ}\!\mathbb{C}$	

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth(j-c)	Channel-to-case thermal resistance	0.29	°C/W
Rth(j-a)	Channel-to-ambient thermal resistance	40	°C/W





DIM	MIN	MAX
Α	19.80	20.20
В	15.40	15.80
C	4.90	5.10
D	0.90	1.10
E	1.40	1.60
F	1.90	2.10
G	10.80	11.00
Н	2.40	2.60
J	0.50	0.70
K	19.50	20.50
P	3.90	4.10
Q	3.30	3.50
U	5.20	5.40
V	2.90	3.10



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#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> =250 μ A	150			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	VDS=VGS; I <sub>D</sub> =250 μ A	3.0		5.0	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> =103A			5.9	mΩ
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = ±20V			±0.1	μА
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =100V; V <sub>GS</sub> = 0V			20	μА
$V_{SD}$	Diode forward voltage	I <sub>S</sub> =103A, V <sub>GS</sub> = 0V			1.3	V

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